FORM PTO-1449 (Modified) U.S Dept. of Commerce (Rev. 7-80) Patent and Trademark Office **INFORMATION DISCLOSURE CITATION** (Use several sheets if necessary)	Atty Docket No. VEON-500 [FOV-123]	Appln. No. 10/621775 NEW
	Applicant(s) EDISON FONG, et al.	
	Filing Date Herewith	Group 2858 ~~Unknown~~

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Examiner	Date Considered
AD/b	10/5/2004

* Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.